

**AMENDMENTS TO THE CLAIMS**

**This listing of claims will replace all prior versions and listings of claims in the application:**

**LISTING OF CLAIMS:**

1. (currently amended): A compound semiconductor light-emitting diode comprising a light-emitting layer composed of a Group III-V compound semiconductor, and a current diffusion layer provided on the light-emitting layer and composed of a Group III-V compound semiconductor, characterized in that the current diffusion layer is composed of a conductive boron-phosphide-based semiconductor and has a bandgap at room temperature wider than that of the light-emitting layer,

wherein the diode includes, in a thickness direction between the current diffusion layer and the light-emitting layer, a cladding layer composed of a Group III-V compound semiconductor, and the cladding layer has a bandgap at room temperature wider than that of the light-emitting layer and equal to or narrower than that of the current diffusion layer, ~~and~~

~~wherein each of the cladding layer and the current diffusion layer are~~ is composed of a boron-phosphide-based semiconductor having a boron compositional gradient such that the bandgap increases from the bottom surface of the ~~cladding~~ current diffusion layer closest to the light-emitting layer ~~to a top surface of the cladding layer and from the top surface of the cladding layer~~ to a top surface of the current diffusion layer,

wherein the cladding layer is composed of a Group III-V compound semiconductor containing aluminum, gallium, and indium, and the current diffusion layer is composed of a

boron-phosphide based semiconductor containing at least one species selected from among aluminum, gallium and indium, and

wherein an Ohmic contact electrode is joined to the current diffusion layer.

2. (original): A compound semiconductor light-emitting diode according to claim 1, wherein the current diffusion layer is composed of at least one species selected from among

boron monophosphide,

boron gallium indium phosphide represented by a compositional formula

$B_{\alpha}Ga_{\gamma}In_{1-\alpha-\gamma}P$  ( $0 < \alpha \leq 1$ ,  $0 \leq \gamma < 1$ ),

boron nitride phosphide represented by a compositional formula  $BP_{1-\delta}N_{\delta}$  ( $0 \leq \delta < 1$ ), and

boron arsenide phosphide represented by a compositional formula  $B_{\alpha}P_{1-\delta}As_{\delta}$ .

3. (previously presented): A compound semiconductor light-emitting diode according to claim 1, wherein the difference between the bandgap at room temperature of the current diffusion layer and the bandgap at room temperature of the light-emitting layer is 0.1 eV or more.

4. (original): A compound semiconductor light-emitting diode according to claim 1, wherein the current diffusion layer has a bandgap at room temperature of 2.8 eV to 5.0 eV.

5. (original): A compound semiconductor light-emitting diode according to claim 1, wherein the current diffusion layer has a carrier concentration at room temperature of  $1 \times 10^{19}$   $\text{cm}^{-3}$  or more, a resistivity at room temperature of  $5 \times 10^{-2} \Omega \cdot \text{cm}$  or less, and a thickness of 50 nm to 5,000 nm.

6. (canceled).

7. (canceled).

8. (canceled).

9. (currently amended): A compound semiconductor light-emitting diode according to claim 1, wherein the light-emitting layer is composed of an aluminum gallium indium phosphide mixed crystal represented by a compositional formula  $\text{Al}_X\text{Ga}_Y\text{In}_Z\text{P}$  ( $0 \leq X, Y, Z \leq 1, X + Y + Z = 1$ ), and ~~at least one of the current diffusion layer and the cladding layer are~~ is composed of an undoped boron-phosphide-based semiconductor to which no impurity element has been intentionally added.

10. (canceled).

11. (currently amended): A compound semiconductor light-emitting diode according to claim 1, wherein ~~the cladding layer and the current diffusing layer have~~ has a bandgap which increases 0.6 eV or more in the thickness direction from the bottom surface of the ~~cladding~~ current diffusion layer ~~closest to the light-emitting layer~~ to the top of the current diffusion layer.

12. (canceled).

13. (canceled).